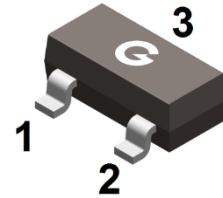
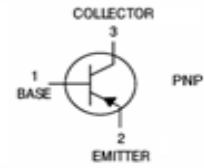


Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$ and corresponding low $R_{CE(sat)}$
- High collector current capability
- High collector current gain
- Improved efficiency due to reduced heat generation

HF



SOT-23

Mechanical Data

- Case: SOT-23
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GT5360	SOT-23	3000 pcs / Tape & Reel	T5360

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Breakdown Voltage	V_{CBO}	-80	V
Collector-Emitter Breakdown Voltage	V_{CEO}	-60	V
Emitter-Base Breakdown Voltage	V_{EBO}	-7	V
Collector Current (Continuous)	I_C	-2	A
Collector Current (Peak)	I_{CM}	-4	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation ($T_A = 25^\circ\text{C}$) *1	P_D	0.46	W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	270	$^\circ\text{C/W}$
Junction Temperature Range	T_J	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note 1: FR-4 @ 100 mm², 1 oz. copper traces

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-80	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-60	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-7	-	-	V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6\text{V}, I_C = 0$	-	-	-0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -10\text{mA}$	150	-	-	-
		$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	150	-	-	-
		$V_{CE} = -2\text{V}, I_C = -1\text{A}$	100	-	-	-
		$V_{CE} = -2\text{V}, I_C = -2\text{A}$	100	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$	-	-	-0.03	V
		$I_C = -1\text{A}, I_B = -100\text{mA}$	-	-	-0.12	V
		$I_C = -2\text{A}, I_B = -200\text{mA}$	-	-	-0.22	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -1\text{A}, I_B = -10\text{mA}$	-	-	-0.9	V
Base-emitter Voltage	$V_{BE(on)}$	$I_C = -1\text{A}, V_{CE} = -2\text{V}$	-	-	-0.85	V
Transition Frequency	f_T	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$ $f = 100\text{MHz}$	100	-	-	MHz

Ratings and Characteristic Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

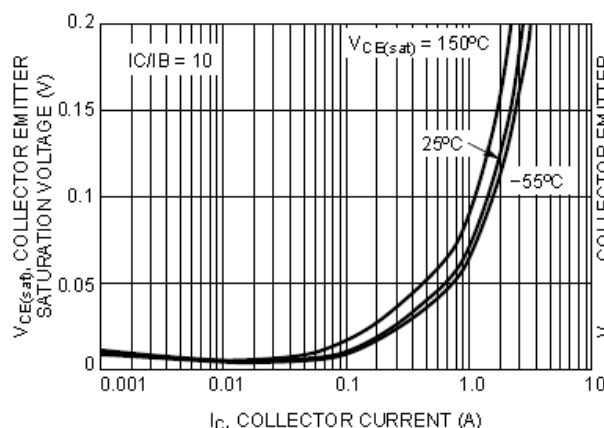


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

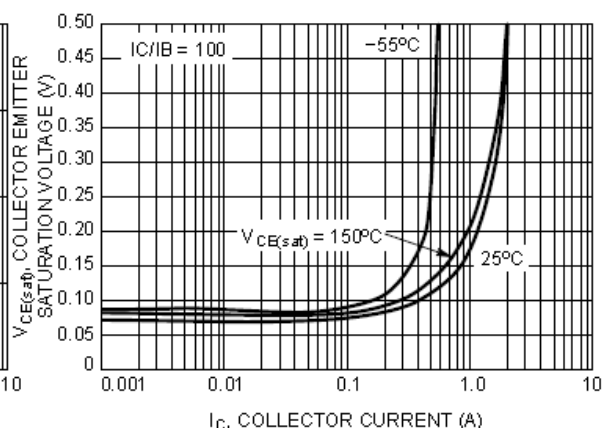


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

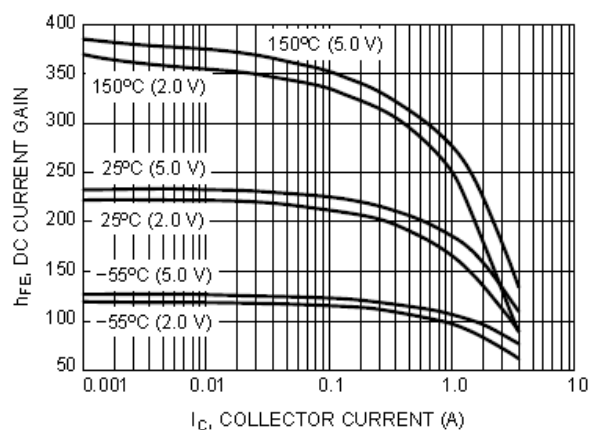


Figure 3. DC Current Gain vs. Collector Current

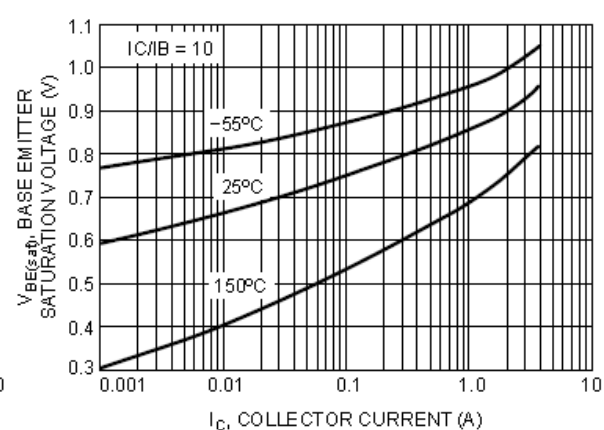


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

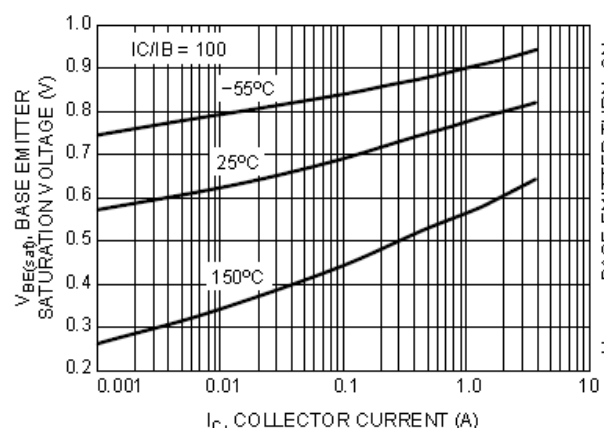


Figure 5. Base Emitter Saturation Voltage vs. Collector Current

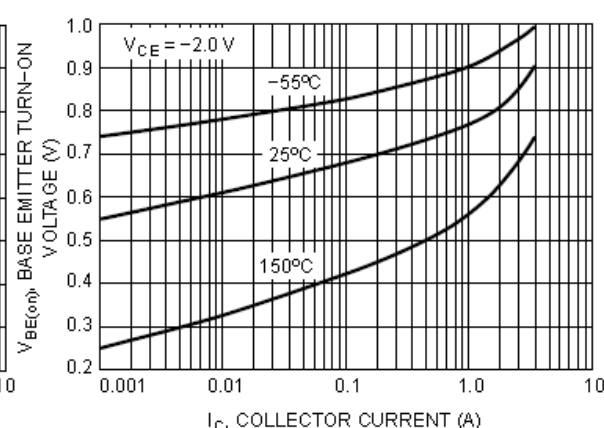
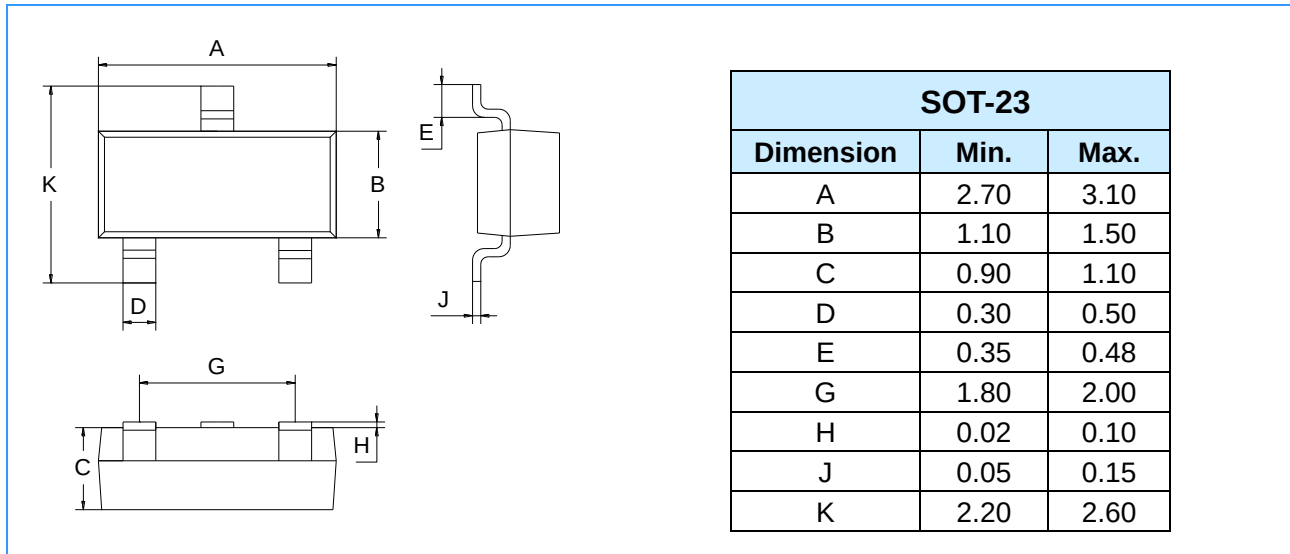
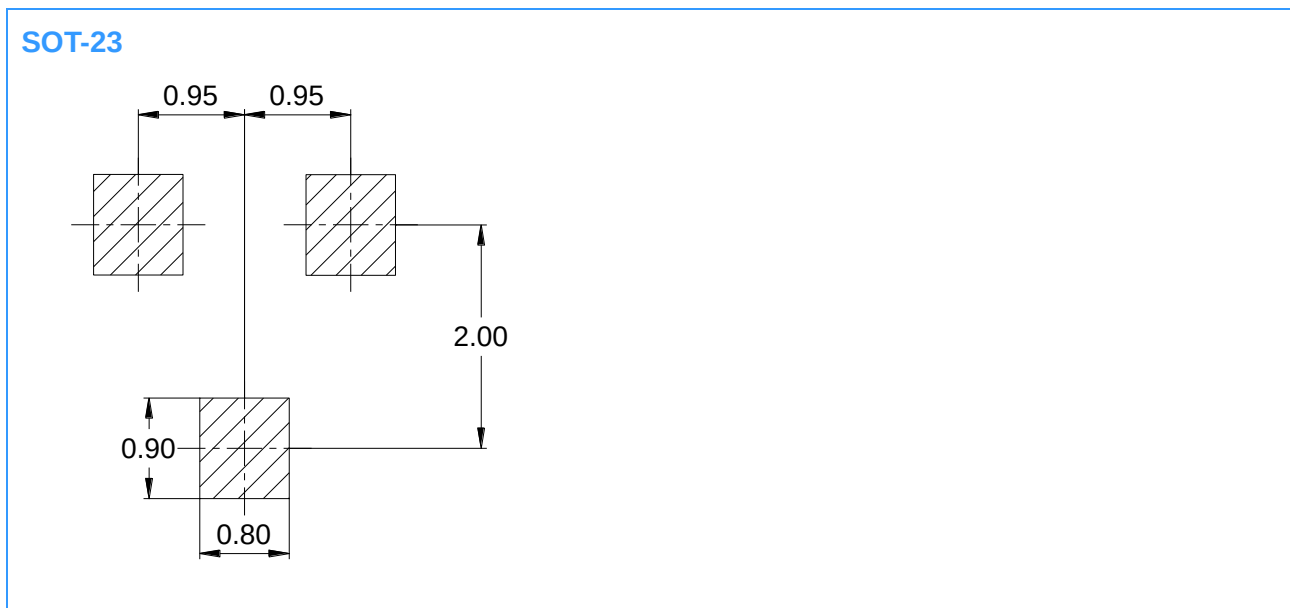


Figure 6. Base Emitter Turn-On Voltage vs. Collector Current

Package Outline Dimensions (Unit: mm)



Package Outline Dimensions (Unit: mm)



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